

Vishay Siliconix

N- and P-Channel 2.5-V (G-S) MOSFET

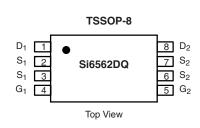
PRODUCT SUMMARY				
	V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	
N-Channel	20	0.030 at V_{GS} = 4.5 V	± 4.5	
		0.040 at V _{GS} = 2.5 V	± 3.9	
P-Channel	- 20	0.050 at V _{GS} = - 4.5 V	± 3.5	
		0.085 at V _{GS} = - 2.5 V	± 2.7	

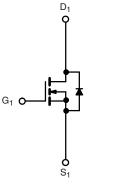
FEATURES

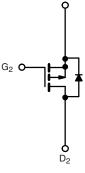
- Halogen-free Option Available
- TrenchFET[®] Power MOSFETS: 2.5 V Rated



RoHS*







S₂

Ordering Information: Si6562DQ-T1 Si6562DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage		V _{DS}	20	- 20	v	
Gate-Source Voltage		V _{GS}	± 12	± 12	v	
Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$	T _A = 25 °C	1	± 4.5	± 3.5		
	T _A = 70 °C	I _D	± 3.6	± 2.7	•	
Pulsed Drain Current		I _{DM}	± 30	± 30	A	
Continuous Source Current (Diode Conduction) ^a		ا _S	1.25	- 1.25		
Maximum Power Dissipation ^a	T _A = 25 °C	P	1.0		w	
	T _A = 70 °C	PD	0.64			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	N- or P-Channel	Unit		
Maximum Junction-to-Ambient ^a	R _{thJA}	125	°C/W		

Notes:

a. Surface Mounted on FR4 board, t \leq 10 s.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static		•			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	N-Ch	h 0.6			v	
		$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	P-Ch	- 0.6			v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$	N-Ch			± 100	nA	
			P-Ch			± 100		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 V, V_{GS} = 0 V$	N-Ch			1	- μΑ	
		$V_{DS} = -20 V, V_{GS} = 0 V$ P				- 1		
		V_{DS} = 20 V, V_{GS} = 0 V, T_{J} = 55 °C	N-Ch			25		
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	P-Ch			- 25		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5$ V, $V_{GS} = 4.5$ V	N-Ch	30			А	
		$V_{DS} \ge$ - 5 V, V_{GS} = - 4.5 V	P-Ch	- 30			A	
	5	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 4.5 \text{ A}$	N-Ch		0.023	0.030		
		V _{GS} = - 4.5 V, I _D = - 3.5 A	P-Ch		0.040	0.050		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 3.9 \text{ A}$	N-Ch		0.030	0.040	Ω	
		V _{GS} = - 2.5 V, I _D = - 2.7 A	P-Ch		0.060	0.085		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 4.5 A	N-Ch		20		S	
		V _{DS} = - 10 V, I _D = - 3.5 A	P-Ch		10			
	V _{SD}	I _S = 1.25 A, V _{GS} = 0 V	N-Ch		0.65	1.2		
Diode Forward Voltage ^a		I _S = - 1.25 A, V _{GS} = 0 V	P-Ch		0.72	- 1.2	V	
Dynamic ^b		•			•	•		
Total Gata Charge	0		N-Ch		13	25		
Total Gate Charge	Qg	N-Channel $V_{DS} = 15 V, V_{GS} = 4.5 V, I_{D} = 4.5 A$	P-Ch		14.5	25	nC	
Gate-Source Charge	Q _{gs}	$v_{\rm DS} = 10$ v, $v_{\rm GS} = 4.0$ v, $i_{\rm D} = 4.0$ A	N-Ch		3.0			
		P-Channel	P-Ch		3.5			
Gate-Drain Charge	Q _{qd}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.5 \text{ A}$	N-Ch		3.3			
	Ŭ		P-Ch N-Ch		3.5 22	50		
Turn-On Delay Time Rise Time	t _{d(on)} t _r	N-Channel	P-Ch		22	50 50		
		V_{DD} = 10 V, R _L = 10 Ω	N-Ch		40	80	ns	
		$I_D \cong$ 1 A, V_{GEN} = 10 V, R_G = 6 Ω	P-Ch		30	60		
Turn-Off Delay Time	t _{d(off)}	P-Channel	N-Ch		50	100		
		$V_{DD} = -10 \text{ V}, \text{ R}_{\text{I}} = 10 \Omega$	P-Ch		57	100		
Fall Time	t _f	$I_D \cong -1 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{G}} = 6 \Omega$	N-Ch		20	40		
	Ч		P-Ch		21	40		
	t _{rr}	I _F = 1.25 A, dl/dt = 100 A/μs Ν			30	60		
Source-Drain Reverse Recovery Time		I _F = - 1.25 A, dl/dt = 100 A/μs	P-Ch		60	100		

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

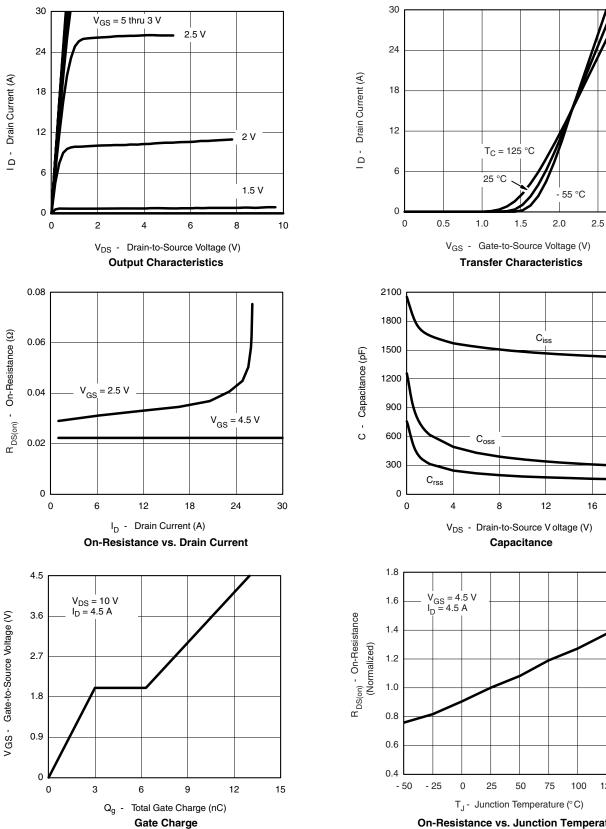
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



3.0

20

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Junction Temperature

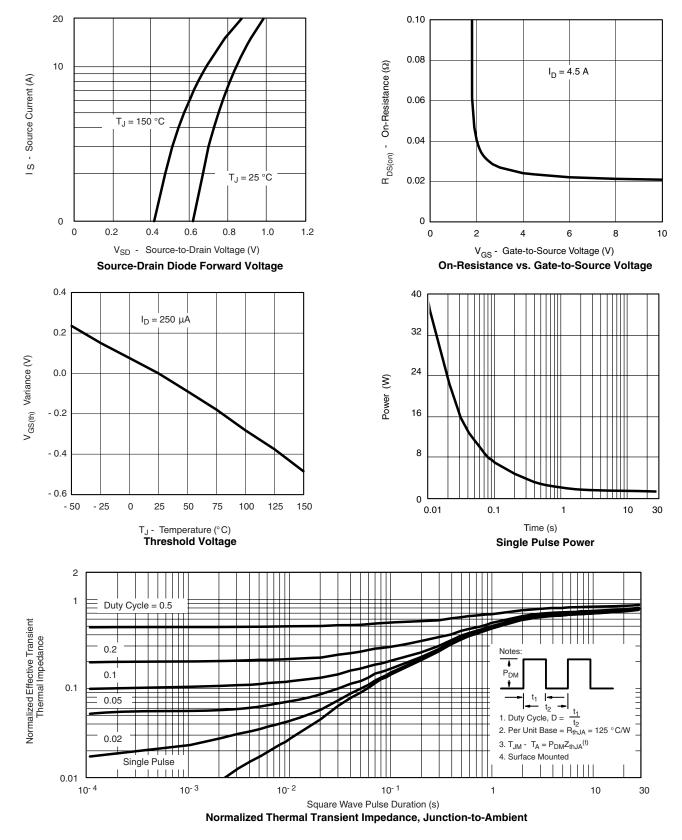
125

150



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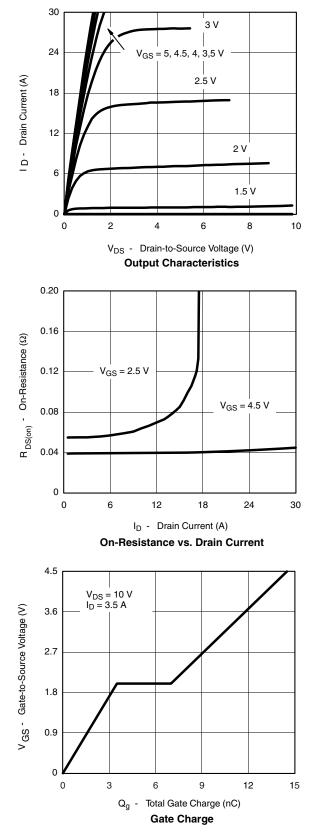
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

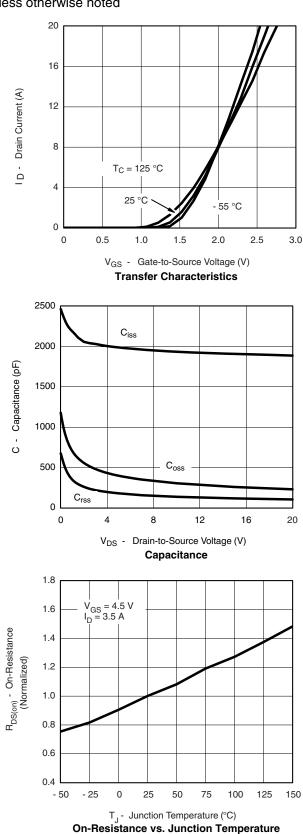




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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



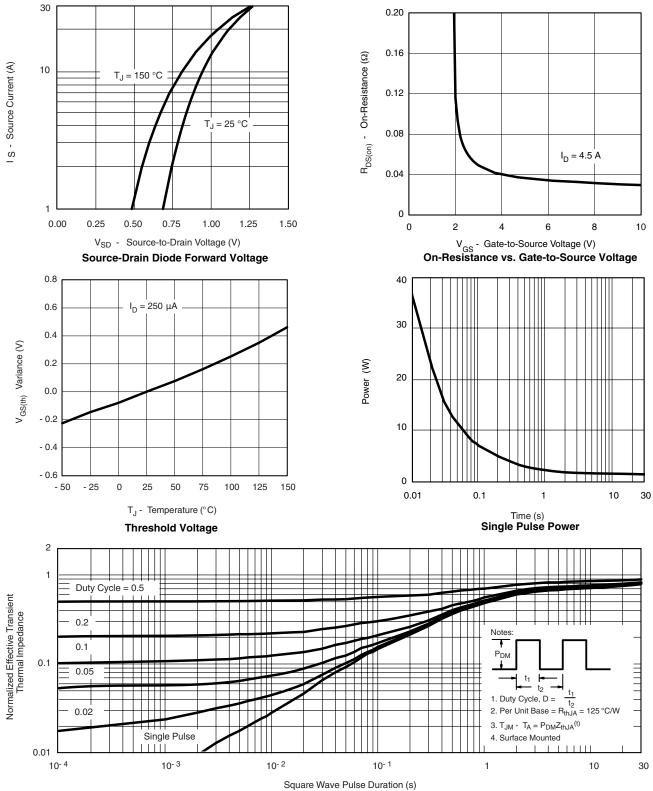


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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?70720.



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